

METHOD AND ARRAY FOR PROCESSING CARRIER MATERIALS BY MEANS OF HEAVY ION RADIATION AND SUBSEQUENT ETCHING

Publication number: WO2004015161

Publication date: 2004-02-19

Inventor: DANZIGER MANFRED (DE)

Applicant: FRACTAL AG (DE); IST
IONENSTRAHLTECHNOLOGIE GMB (DE); DANZIGER
MANFRED (DE)

Classification:





- international: *B01D67/00; B26F1/26; B29C59/16; C23C14/02;
H05K3/38; B01D67/00; B26F1/00; B29C59/00;
C23C14/02; H05K3/38; (IPC1-7): C23C14/02; B26F1/26;
B29C59/16; B32B31/00; H01G9/04; H01J37/31*

- european: B01D67/00H10F; B26F1/26; B29C59/16; B32B38/00B;
C23C14/02A2






Application number: WO2003DE02533 20030723

Priority number(s): DE20021034614 20020724

Also published as:

 US2005230353 (A1)
 EP1525334 (A0)
 AU2003258471 (A1)
 DE10234614 (B3)

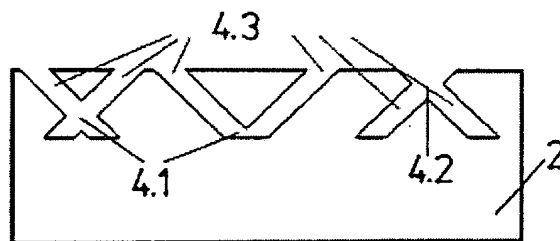
Cited documents:

 WO0242514
 US6015976
 US5350499
 EP0875360
 DD297175
more >>

Report a data error here

Abstract of WO2004015161

The invention relates to a method and an array for processing carrier materials by means of heavy ion radiation and subsequent etching, wherein the heavy ion radiation is carried out in such a way that a ray beam (1) of an energy-rich heavy ion radiation (1.1) incides on the surface (2) of a carrier material in at least two different angles. According to the invention, the fluence, the energy and the direction of incidence of the heavy ion rays (1.1) are selected in such a way that a maximum amount of intersecting or coinciding latent ion traces (3) and common numbers of incisions of the recesses (4) resulting from a chemical etching process following heavy ion radiation are obtained.



Data supplied from the esp@cenet database - Worldwide